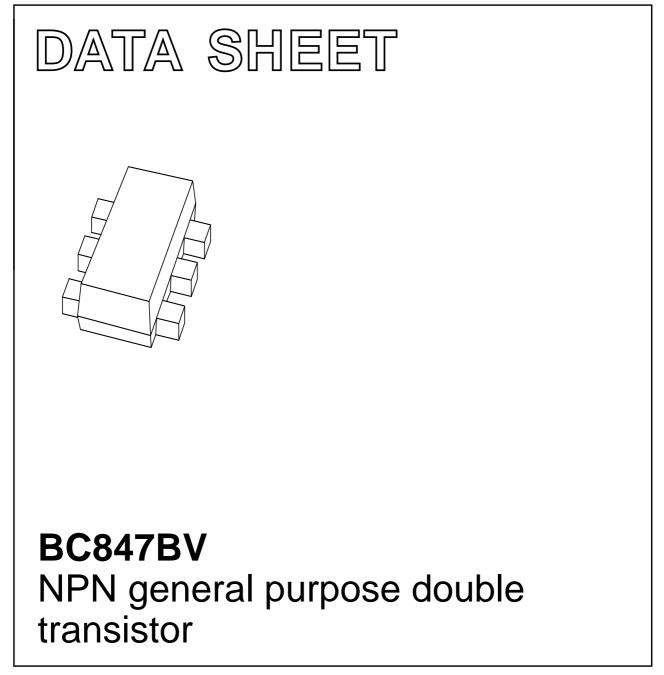
DISCRETE SEMICONDUCTORS



Product specification

2001 Sep 10



FEATURES

- 300 mW total power dissipation
- Very small 1.6 mm \times 1.2 mm \times 0.55 mm ultra thin package
- · Excellent coplanarity due to straight leads
- · Low collector capacitance
- · Improved thermal behaviour due to flat leads
- Reduces number of components as replacement of two SC-75/SC-89 packaged BISS transistors
- · Reduces required board space
- · Reduces pick and place costs.

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

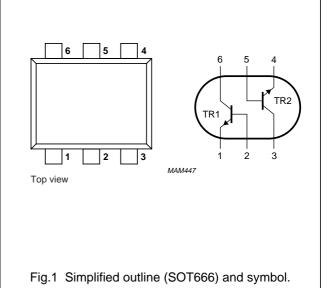
NPN double transistor in a SOT666 plastic package. PNP complement: BC857BV.

MARKING

TYPE NUMBER	MARKING CODE
BC847BV	1F

PINNING

PIN	DESCRIPTION			
1, 4	emitter	TR1; TR2		
2, 5	base	TR1; TR2		
6, 3	collector	TR1; TR2		



BC847BV

BC847BV

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transi	stor				
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	45	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current (DC)		-	100	mA
I _{CM}	peak collector current		-	200	mA
I _{BM}	peak base current		-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C
Per device	9	•			
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	300	mW

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

Notes

- 1. Transistor mounted on an FR4 printed-circuit board.
- 2. The only recommended soldering method is reflow soldering.

BC847BV

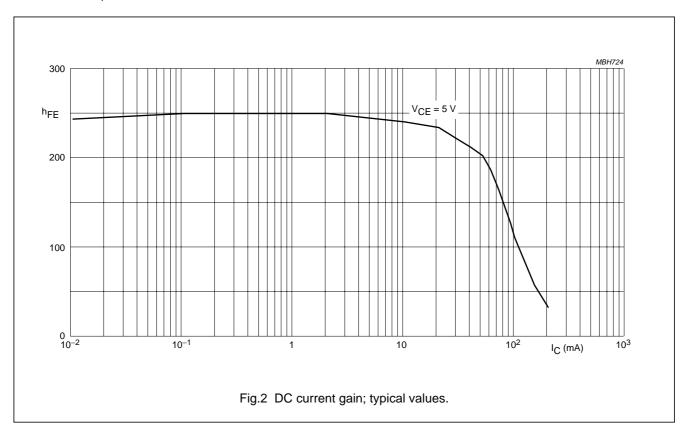
CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

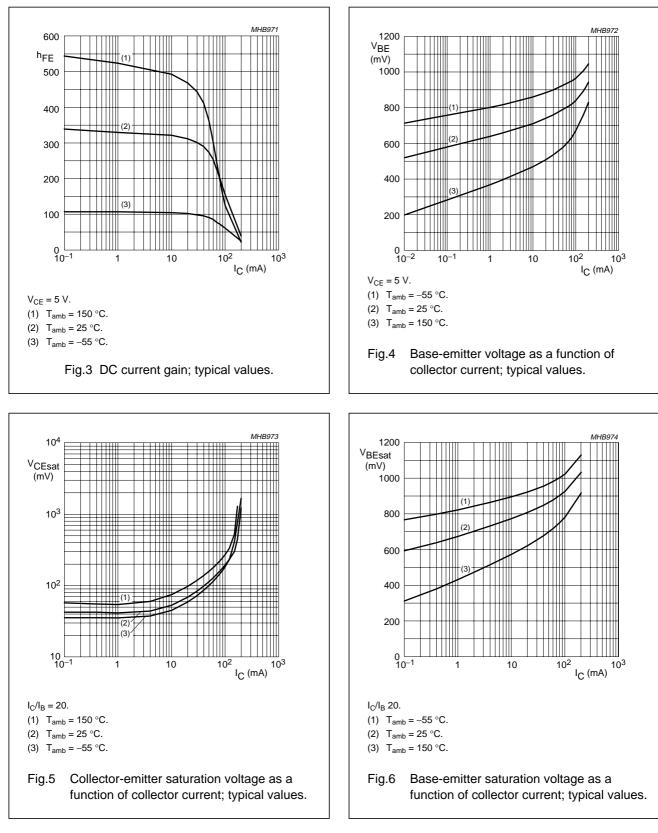
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transis	stor					
I _{CBO}	collector-base cut-off current	I _E = 0; V _{CB} = 30 V	_	-	15	nA
		$I_E = 0; V_{CB} = 30 \text{ V}; T_j = 150 ^{\circ}\text{C}$	_	-	5	μA
I _{EBO}	emitter-base cut-off current	$I_{C} = 0; V_{EB} = 5 V$	_	-	100	nA
h _{FE}	DC current gain	$I_{C} = 2 \text{ mA}; V_{CE} = 5 \text{ V}$	200	-	450	
V _{BE}	base-emitter voltage	$I_{C} = 2 \text{ mA}; V_{CE} = 5 \text{ V}$	580	655	700	mV
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C}$ = 10 mA; $I_{\rm B}$ = 0.5 mA	-	-	100	mV
		$I_{C} = 100 \text{ mA}; I_{B} = 5 \text{ mA}; \text{ note } 1$	-	-	300	mV
V _{BEsat}	base-emitter saturation voltage	$I_{\rm C}$ = 10 mA; $I_{\rm B}$ = 0.5 mA	_	755	-	mV
C _c	collector capacitance	$I_E = I_e = 0; V_{CB} = 10 V; f = 1 MHz$	-	-	1.5	pF
C _e	emitter capacitance	$I_{C} = i_{c} = 0; V_{EB} = 500 \text{ mV;} f = 1 \text{ MHz}$	_	11	-	pF
f _T	transition frequency	I_{C} = 10 mA; V_{CE} = 5 V; f = 100 MHz	100	-	_	MHz

Note

1. Pulse test: $t_p \leq 300 \ \mu s; \ \delta \leq 0.02.$

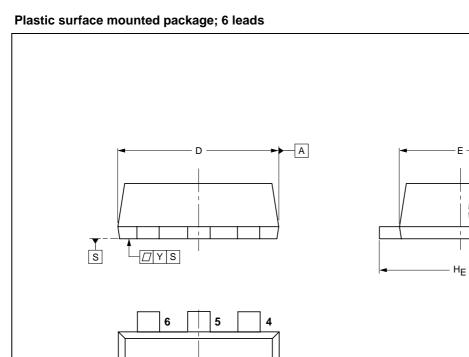


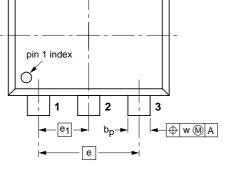
BC847BV

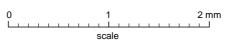


Graphical information BC847BV

PACKAGE OUTLINE







Α

DIMENSIONS (mm are the original dimensions)

UNIT	Α	bp	с	D	Е	e	e ₁	H _E	Lp	w	у
mm	0.6 0.5	0.27 0.17	0.18 0.08	1.7 1.5	1.3 1.1	1.0	0.5	1.7 1.5	0.3 0.1	0.1	0.1

OUTLINE	OUTLINE REFERENCES				EUROPEAN	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						-01-01-04 01-08-27

BC847BV

X

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detail X

SOT666

BC847BV

DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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